

Form PTO 1449 (Rev. 2-32)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 034299-617	Serial No. 10/520,647
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Information Disclosure Statement by Applicant		Applicant: Marie D'Angelo, et al.	
(Use several sheets if necessary)		Filed: January 5, 2005	Group: (to be assigned)

U.S. Patent Documents							
Init.		Document No.	Date	Name	Class	Subclass	Filing Date
/TC/	A	US2004/0132242	7/8/04	D'Angelo et al.			
	B	3,998,662	12/21/76	Anthony et al.			
	C	4,735,921	4/5/88	Soukiassian			
	D	4,900,710	2/13/90	Soukiassian et al.			
↓	E	6,274,234	8/14/01	Dujardin et al.			
	F	6,667,102	12/23/03	Amy et al.			

Foreign Documents								Translation	
Init.		Document No.	Date	Country	Class	Subclass	Yes	No	
/TC/	G	2 757 183	12/16/96	France					X
/TC/	H	2 786 794	12/2/98	France (w/English Abstract)					X

Other Documents (Including Author, Title, Date, Pertinent Pages, etc.)							
/TC/	I	Crommie, M.F. et al., "Waves on a Metal Surface and Quantum Corrals", <i>Surface Review and Letters</i> , Vol. 2, No. 1, pages 127-137 (1995)					
	J	Franciosi, A. et al., "Electronic promoters and semiconductor oxidation: Alkali metals on Si(111) surfaces", <i>Physical Review B</i> , Vol. 35, No. 2, pages 910-913 (1987)					
	K	Gentle, T. M., "CH ₃ Cl Adsorption on a Si(100)2 X 1 Surface Modified by Alkali Metal Overlayer Studied by Soft X-Ray Photoemission Using Synchrotron Radiation", <i>Surface Science Letters</i> 202, pages 568-576 (1988)					
	L	Huttel, Y. et al., "Al ₂ O _{3+x} /Al interface formation by promoted oxidation using an alkali metal and removal of the catalyst", <i>Applied Physics Letters</i> 62, pages 2437-2439 (1993)					
	M	Riehl-Chudoba, M. et al., "Direct and Rb-promoted SiO _x /β-SiC(100) interface formation", <i>Physical Review B</i> , Vol. 51, No. 20, pages 14300-14310 (1995)					
	N	Shen, T.C., et al., "Atomic-Scale Desorption Through Electronic and Vibrational Excitation Mechanisms", <i>Science</i> , Vol. 268, pages 1590-1592 (1995)					
	O	Soukiassian, P., "Alkali Metals and Semiconductor Surfaces: Electronic, Structural and Catalytic Properties", <i>Physics and Chemistry of Alkali Metal Adsorption</i> , Elsevier Science Publishers B.V., pages 449-467 (1989)					
	P	Soukiassian, P., et al., "Catalytic Nitridation of a III-V Semiconductor Using Alkali Metal", <i>Europhysics Letters</i> 12, pages 87-92 (1990)					
	Q	Soukiassian, P., et al., "Catalytic Oxidation of Semiconductors by Alkali Metals", <i>Physica Scripta</i> , Vol. 35, pages 757-760 (1987)					
↓	R	Soukiassian, P., et al., "Electronic Promotion of Silicon Nitridation by Alkali Metals", <i>Physical Review Letters</i> , Vol. 59, No. 13, pages 1488-1491 (1987)					
Examiner	/Tsz Chiu/ (10/01/2007)				Date Considered 10/01/2007		

Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.

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/TC/	S	Soukiassian, P., et al., "Electronic properties of O ₂ on Cs or Na overlayers adsorbed on Si(100) 2 x 1 from room temperature to 650° C", <i>Physical Review B</i> , Vol. 35, No. 8, pages 4176-4179 (1987)		
	T	Soukiassian, P., et al., "Exceptionally large enhancement of InP (110) oxidation rate by cesium catalyst", <i>Journal of Applied Physics</i> 61, pages 2679-2681 (1987)		
	U	Soukiassian, P., et al., "Rb- and K-promoted nitridation of cleaved GaAs and InP surfaces at room temperature", <i>Applied Surface Science</i> 56-58, pages 772-776 (1992)		
	V	Soukiassian, P., et al., "Room-temperature nitridation of gallium arsenide using alkali metal and molecular nitrogen", <i>Physical Review B</i> , Vol. 42, No. 6, pages 3769-3772 (1990)		
	W	Soukiassian, P., et al., "Si ₃ N ₄ -Si interface formation by catalytic nitridation using nitrogen exposures on alkali metal overlayers and removal of the catalyst: N ₂ /Na/Si(100) 2X1", <i>Applied Physics Letters</i> 51, pages 346-348 (1987)		
	X	Soukiassian, P., et al., "SiO ₂ -Si interface formation by catalytic oxidation using alkali metals and removal of the catalyst species", <i>Journal of Applied Physics</i> 60, pages 4339-4341 (1986)		
	Y	Starnberg, H.I., "Alkali-metal-promoted oxidation of the Si(100)2X1 surface: Coverage dependence and nonlocality", <i>Physical Review B</i> , Vol. 39, No. 17, pages 12775-12782 (1989)		
	Z	Starnberg, H.I., "Thermal growth of SiO ₂ -Si interfaces on a Si(111)7X7 surface modified by cesium", <i>Physical Review B</i> , Vol. 37, No. 3, pages 1315-1319 (1988)		
	AA	Sugioka, Koji, et al., "Novel Technology for Laser Precision Microfabrication of Hard Materials", <i>Proceedings of the SPIE, SPIE, Bellingham, WA</i> , Vol. 4088, pages 110-117 (2000)		
↓	AB	Whitman, L.J., et al., "Manipulation of Adsorbed Atoms and Creation of New Structures on Room-Temperature Surfaces with a Scanning Tunneling Microscope", <i>Science</i> , Vol. 251, pages 1206-1210 (1991)		
Examiner		Date Considered		10/01/2007
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